Low Noise Transistors PNP Silicon

MAXIMUM RATINGS

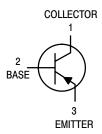
Rating	Symbol	BC559	BC560	Unit
Collector–Emitter Voltage	V _{CEO}	-30	-45	Vdc
Collector-Base Voltage	V _{CBO}	-30	-50	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0		Vdc
Collector Current — Continuous	I _C	-100		mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0		mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

BC559, B, C BC560C





$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}\text{C unless otherwise noted})$

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I _C = -10 mAdc, I _B = 0)	BC559 BC560	V _{(BR)CEO}	-30 -45			Vdc
Collector–Base Breakdown Voltage ($I_C = -10 \mu Adc, I_E = 0$)	BC559 BC560	V _{(BR)CBO}	-30 -50	_ _	_ _	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \mu Adc$, $I_C = 0$)		V _{(BR)EBO}	-5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -30 \text{ Vdc}, I_E = 0, T_A = +125^{\circ}\text{C})$		I _{CBO}			-15 -5.0	nAdc μAdc
Emitter Cutoff Current (V _{EB} = -4.0 Vdc, I _C = 0)		I _{EBO}	_	_	-15	nAdc

BC559, B, C BC560C

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS		4		1		I
DC Current Gain ($I_C = -10 \mu Adc$, $V_{CE} = -5.0 Vdc$) ($I_C = -2.0 \text{ mAdc}$, $V_{CE} = -5.0 Vdc$)	BC559B BC559C/560C BC559B BC559C/560C BC559	h _{FE}	100 100 180 380 120	150 270 290 500	 460 800 800	_
Collector–Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -10$ mAdc, $I_B = \text{see note 1}$) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc, see note 2)		V _{CE(sat)}	_ _ _	-0.075 -0.3 -0.25	-0.25 -0.6 	Vdc
Base–Emitter Saturation Voltage $(I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$		V _{BE(sat)}	_	-1.1	_	Vdc
Base–Emitter On Voltage $ \begin{aligned} &(I_C = -10 \; \mu\text{Adc}, \; V_{CE} = -5.0 \; \text{Vdc}) \\ &(I_C = -100 \; \mu\text{Adc}, \; V_{CE} = -5.0 \; \text{Vdc}) \\ &(I_C = -2.0 \; \text{mAdc}, \; V_{CE} = -5.0 \; \text{Vdc}) \end{aligned} $		V _{BE(on)}	 _0.55	-0.52 -0.55 -0.62	 	Vdc
SMALL-SIGNAL CHARACTERISTICS		1				•
Current-Gain — Bandwidth Product (I _C = -10 mAdc, V _{CE} = -5.0 Vdc, f = 100 MHz	:)	f _T	_	250	_	MHz
Collector–Base Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)		C _{cbo}	_	2.5	_	pF
Small–Signal Current Gain ($I_C = -2.0 \text{ mAdc}$, $V_{CE} = -5.0 \text{ V}$, $f = 1.0 \text{ kHz}$)	BC559B BC559C/BC560C	h _{fe}	240 450	330 600	500 900	_
Noise Figure (I _C = $-200 \mu Adc$, V _{CE} = $-5.0 Vdc$, R _S = $2.0 k\Omega$ (I _C = $-200 \mu Adc$, V _{CE} = $-5.0 Vdc$, R _S = $100 k\Omega$,	NF ₁ NF ₂	_	0.5	2.0 10	dB

NOTES:

^{1.} I_B is value for which I_C = -11 mA at V_{CE} = -1.0 V. 2. Pulse test = 300 μ s - Duty cycle = 2%.

BC559, B, C BC560C

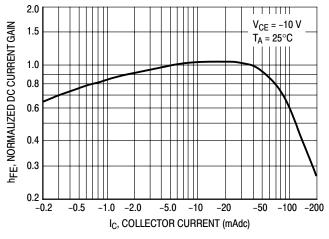


Figure 1. Normalized DC Current Gain

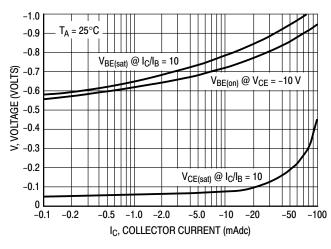


Figure 2. "Saturation" and "On" Voltages

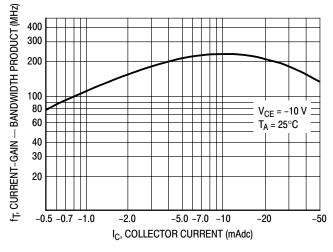


Figure 3. Current-Gain — Bandwidth Product

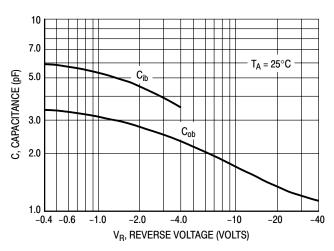


Figure 4. Capacitance

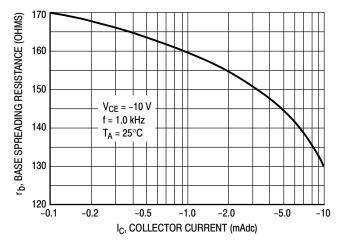
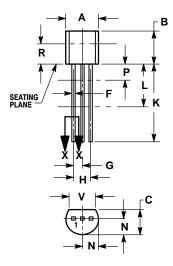


Figure 5. Base Spreading Resistance

PACKAGE DIMENSIONS

CASE 029-04 (TO-226AA) ISSUE AD





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L.
 DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 17:

PIN 1. COLLECTOR 2. BASE EMITTER

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